

Product Summary

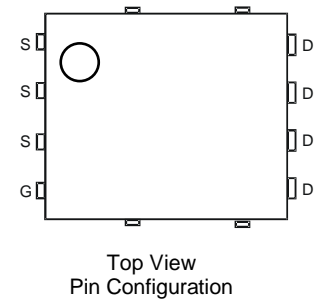
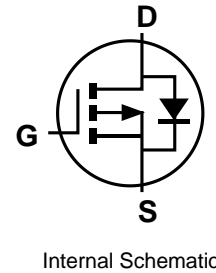
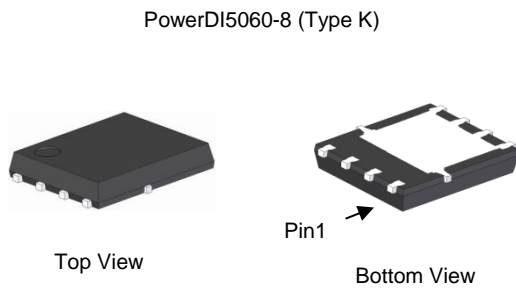
BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
-20V	2.5mΩ @ V _{GS} = -10V	-60A
	3.5mΩ @ V _{GS} = -4.5V	-60A

Description

This new generation P-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance.

Applications

- Load Switch
- Notebook Battery Power Management

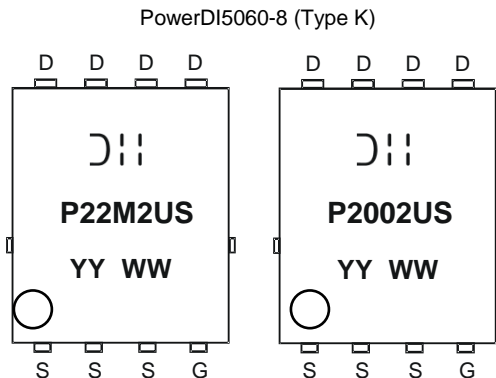


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP22M2UPS-13	PowerDI5060-8 (Type K)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 P22M2US or P2002US = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 21 = 2021)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current, V _{GS} = 10V (Note 5)	Steady State (Note 6)	I _D	T _C = +25°C	-60	A
			T _C = +70°C	-60	A
			T _A = +25°C	-42	A
			T _A = +70°C	-33.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-100	A	
Continuous Body Diode Forward Current (Note 5)	Steady State (Note 6)	I _S	T _C = +25°C	-60	A
			T _A = +25°C	-5.6	A
Avalanche Current, L = 0.1mH		I _{AS}	-37	A	
Avalanche Energy, L = 0.1mH		E _{AS}	69.8	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	55	°C/W
Total Power Dissipation (Note 6)	Steady State	P _D	104	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	0.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
6. Package limited.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-10	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	—	-1.4	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	2.5	mΩ	V _{GS} = -10V, I _D = -25A
		—	—	3.5		V _{GS} = -4.5V, I _D = -20A
		—	—	5.0		V _{GS} = -2.5V, I _D = -15A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	12826	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	2547	—		
Reverse Transfer Capacitance	C _{rss}	—	1924	—		
Gate Resistance	R _G	—	4.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	476	—	nC	V _{DS} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	228	—		
Gate-Source Charge	Q _{gs}	—	24.8	—		
Gate-Drain Charge	Q _{gd}	—	61.9	—		
Turn-On Delay Time	t _{D(ON)}	—	14.2	—	ns	V _{DD} = -10V, V _{GEN} = -4.5V, R _{GEN} = 1Ω, I _D = -10A
Turn-On Rise Time	t _R	—	35.4	—		
Turn-Off Delay Time	t _{D(OFF)}	—	361	—		
Turn-Off Fall Time	t _F	—	224	—		
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V _{SD}	—	-0.58	—	V	V _{GS} = 0V, I _S = -5A
Reverse Recovery Time (Note 8)	t _{RR}	—	137	—	ns	I _F = -10A, di/dt = 100A/μs
Reverse Recovery Charge (Note 8)	Q _{rr}	—	221	—	nC	
Reverse Recovery Fall Time (Note 8)	t _a	—	39	—	ns	
Reverse Recovery Rise Time (Note 8)	t _b	—	98	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

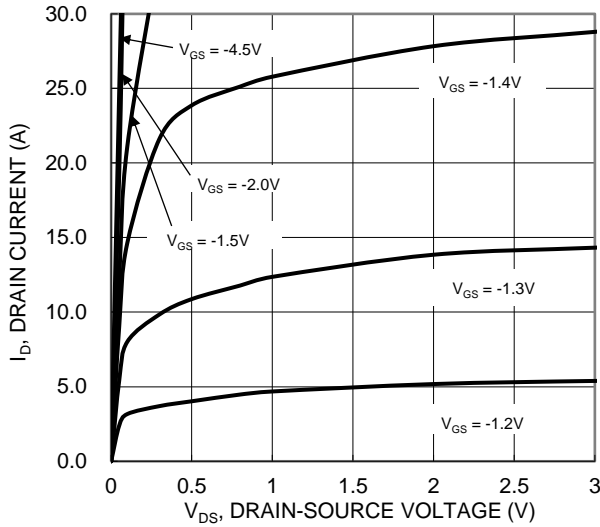


Figure 1. Typical Output Characteristic

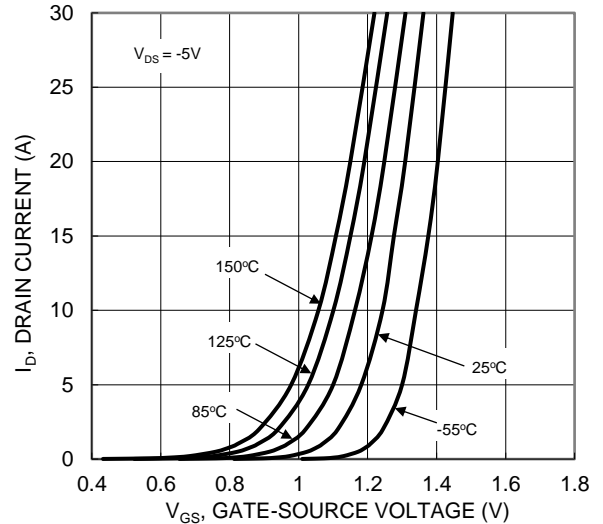


Figure 2. Typical Transfer Characteristic

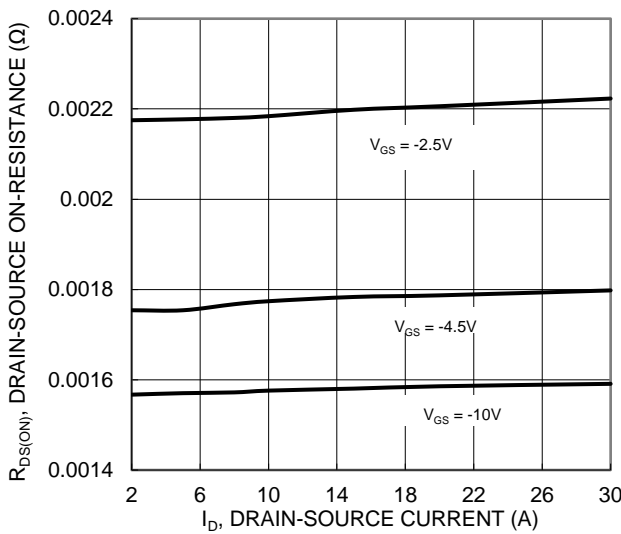


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

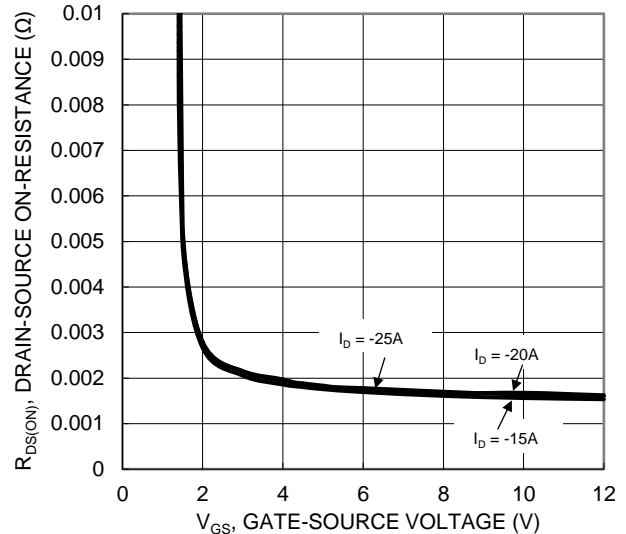


Figure 4. Typical Transfer Characteristic

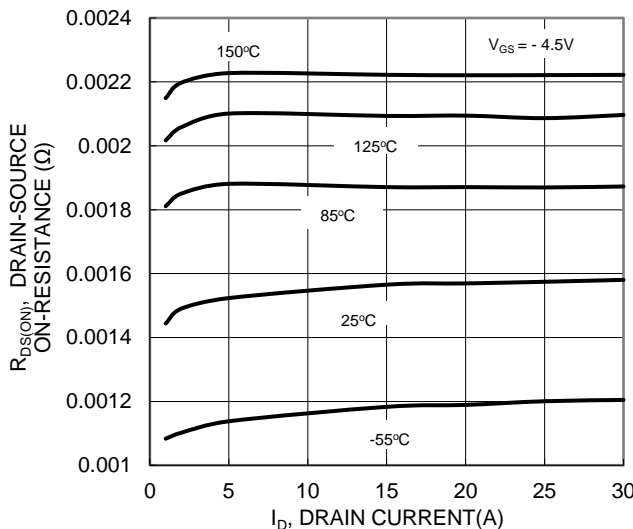


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

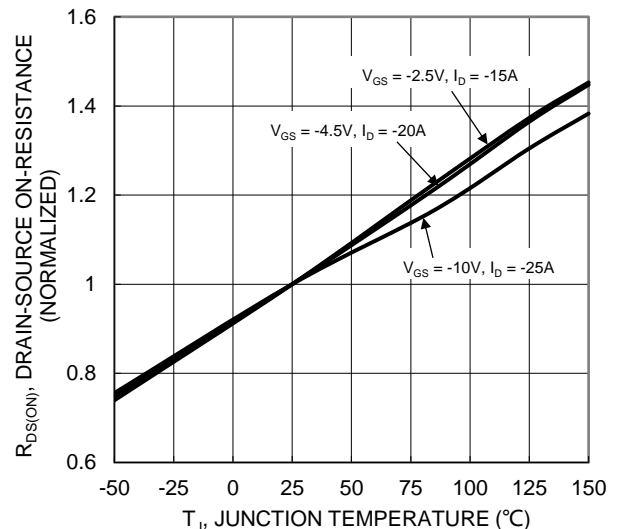


Figure 6. On-Resistance Variation with Temperature

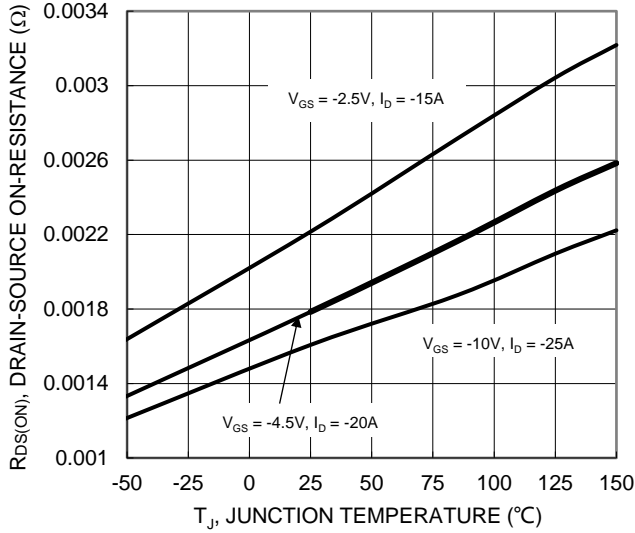


Figure 7. On-Resistance Variation with Temperature

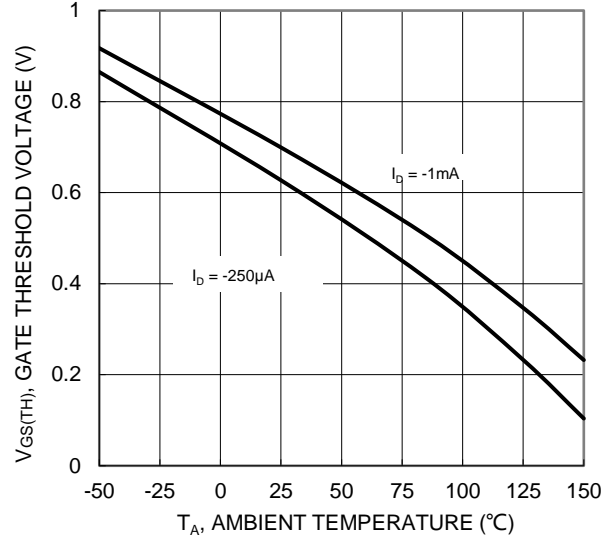


Figure 8. Gate Threshold Variation vs. Ambient Temperature

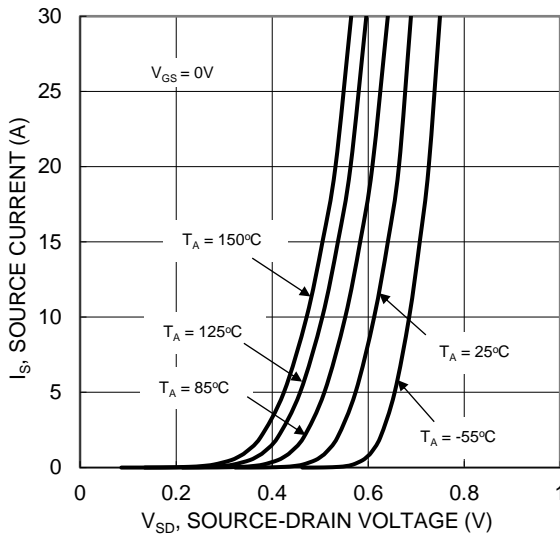


Figure 9. Diode Forward Voltage vs. Current

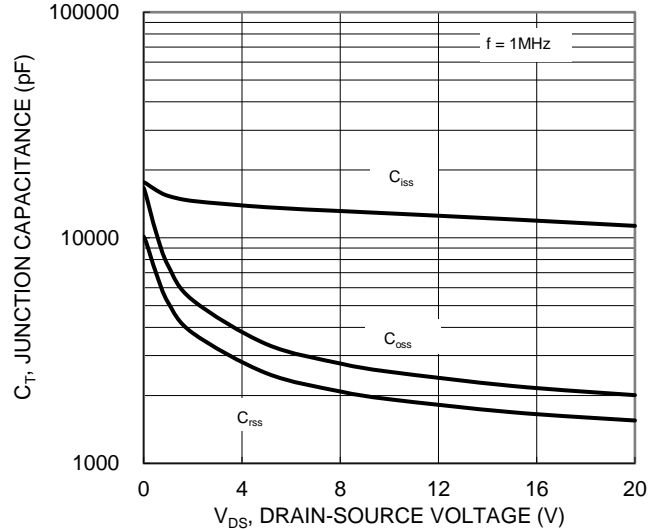


Figure 10. Typical Junction Capacitance

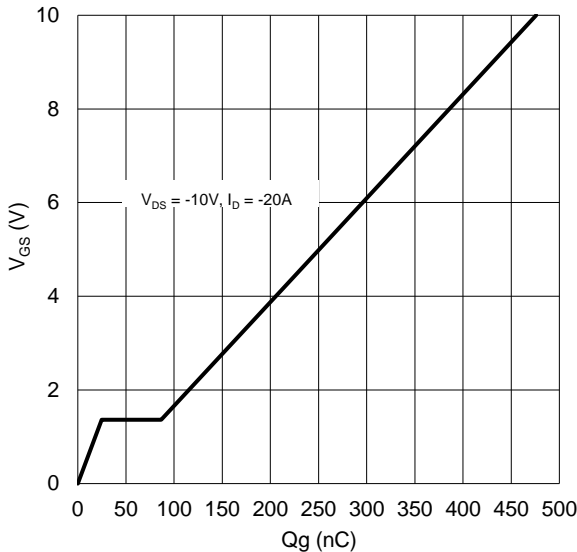


Figure 11. Gate Charge

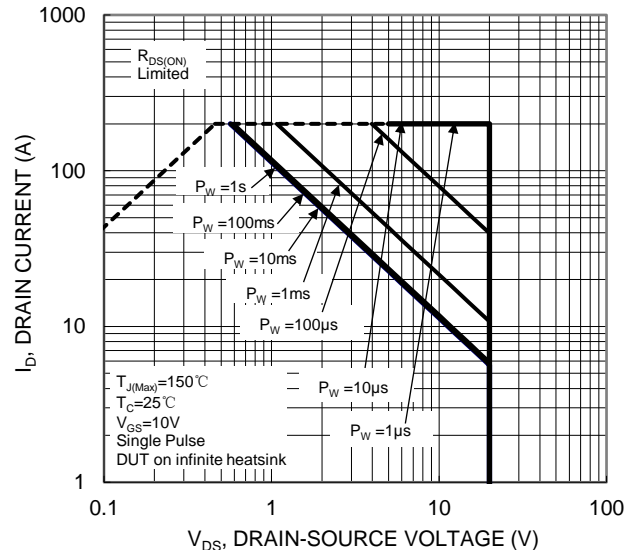


Figure 12. SOA, Safe Operation Area

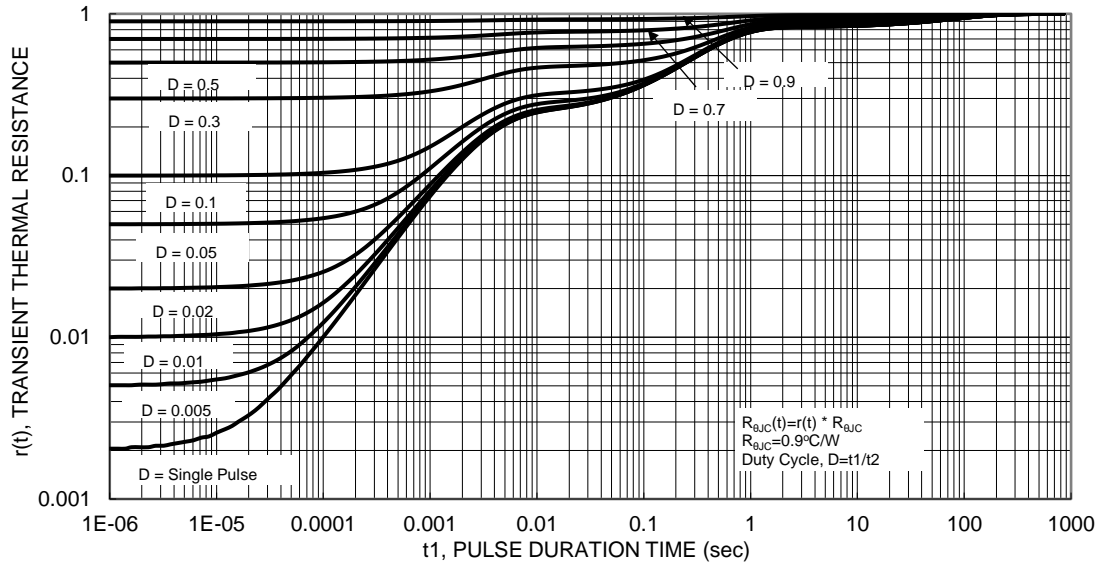
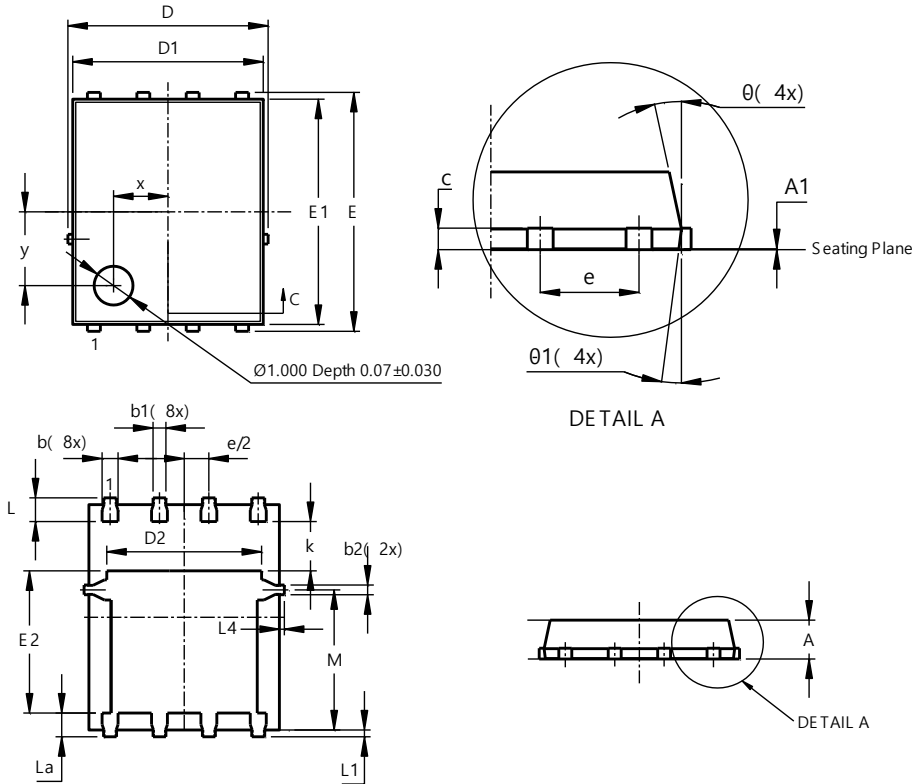


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

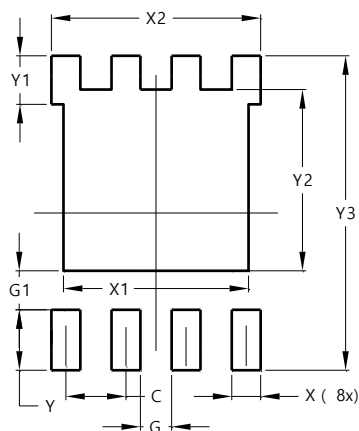


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
e	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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